### FAIRCHILD

SEMICONDUCTOR

### MM74HCT00 Quad 2 Input NAND Gate

### **General Description**

The MM74HCT00 is a NAND gates fabricated using advanced silicon-gate CMOS technology which provides the inherent benefits of CMOS—low quiescent power and wide power supply range. This device is input and output characteristic and pin-out compatible with standard 74LS logic families. All inputs are protected from static discharge damage by internal diodes to V<sub>CC</sub> and ground.

MM74HCT devices are intended to interface between TTL and NMOS components and standard CMOS devices. These parts are also plug-in replacements for LS-TTL devices and can be used to reduce power consumption in existing designs.

### February 1984 Revised January 2005

- TTL, LS pin-out and threshold compatible
- Fast switching: t<sub>PLH</sub>, t<sub>PHL</sub>=14 ns (typ)

**Features** 

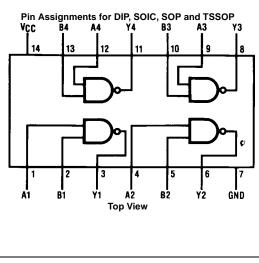
- Low power: 10 µW at DC
- High fan out, 10 LS-TTL loads

### **Ordering Code:**

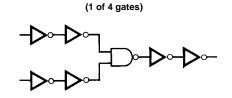
Order Number	Package	Package Description			
Order Number	Number	i ackage bescription			
MM74HCT00M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow			
MM74HCT00MX_NL	M14A	Pb-Free 14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow			
MM74HCT00SJ	M14D	Pb-Free 14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide			
MM74HCT00MTC	MTC14	14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide			
MM74HCT00MTCX_NL MTC14 Pb-Free 14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4 Wide					
MM74HCT00N	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide			
MM74HCT00N_NL	N14A	Pb-Free 14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide			
Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.					

Pb-Free package per JEDEC J-STD-020B.

### **Connection Diagram**



### Logic Diagram



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# MM74HCT00

### Absolute Maximum Ratings(Note 1) (Note 2)

Supply Voltage (V <sub>CC</sub> )	-0.5 to +7.0V
DC Input Voltage (V <sub>IN</sub> )	$-1.5$ to $V_{CC}\mbox{+}1.5\mbox{V}$
DC Output Voltage (V <sub>OUT</sub> )	–0.5 to $V_{CC}\mbox{+}0.5\mbox{V}$
Clamp Diode Current (I <sub>IK</sub> , I <sub>OK</sub> )	±20 mA
DC Output Current, per pin (I <sub>OUT</sub> )	±25 mA
DC V <sub>CC</sub> or GND Current, per pin (I <sub>CC</sub> )	±50 mA
Storage Temperature Range (T <sub>STG</sub> )	$-65^{\circ}C$ to $+150^{\circ}C$
Power Dissipation (P <sub>D</sub> )	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature (T <sub>L</sub> )	
(Soldering 10 seconds)	260°C

## Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V <sub>CC</sub> )	4.5	5.5	V
DC Input or Output Voltage	0	V <sub>CC</sub>	V
(V <sub>IN</sub> , V <sub>OUT</sub> )			
Operating Temperature Range $(T_A)$	-40	+85	°C
Input Rise or Fall Times			
(t <sub>r</sub> , t <sub>f</sub> )		500	ns
<b>Note 1:</b> Absolute Maximum Ratings are those age to the device may occur.	e values	beyond wł	nich dam-

Note 2: Unless otherwise specified all voltages are referenced to ground. Note 3: Power Dissipation temperature derating — plastic "N" package: – 12 mW/°C from 65°C to 85°C.

### **DC Electrical Characteristics**

### $V_{CC}$ = 5V $\pm$ 10% (unless otherwise specified)

Symbol	Parameter	Conditions	T <sub>A</sub> = 25°C		$T_A = -40$ to $85^{\circ}C$	$T_A = -55$ to $125^{\circ}C$	Units
Symbol			Тур		Guaranteed Limits		Units
VIH	Minimum HIGH Level			2.0	2.0	2.0	V
	Input Voltage						
VIL	Maximum LOW Level			0.8	0.8	0.8	V
	Input Voltage						
V <sub>OH</sub>	Minimum HIGH Level	$V_{IN} = V_{IH}$ or $V_{IL}$					
	Output Voltage	$ I_{OUT}  = 20 \ \mu A$	V <sub>CC</sub>	V <sub>CC</sub> -0.1	V <sub>CC</sub> -0.1	V <sub>CC</sub> -0.1	V
		$ I_{OUT}  = 4.0 \text{ mA}, V_{CC} = 4.5 \text{V}$	4.2	3.98	3.84	3.7	V
		$ I_{OUT}  = 4.8 \text{ mA}, V_{CC} = 5.5 \text{V}$	5.2	4.98	4.84	4.7	V
V <sub>OL</sub>	Maximum LOW Level	$V_{IN} = V_{IH}$					
	Voltage	$ I_{OUT}  = 20 \ \mu A$	0	0.1	0.1	0.1	V
		$ I_{OUT}  = 4.0 \text{ mA}, V_{CC} = 4.5 \text{V}$	0.2	0.26	0.33	0.4	V
		$ I_{OUT}  = 4.8 \text{ mA}, V_{CC} = 5.5 \text{V}$	0.2	0.26	0.33	0.4	V
I <sub>IN</sub>	Maximum Input	$V_{IN} = V_{CC}$ or GND,		±0.05	±0.5	±1.0	μΑ
	Current	V <sub>IH</sub> or V <sub>IL</sub>					
I <sub>CC</sub>	Maximum Quiescent	$V_{IN} = V_{CC}$ or GND,		1.0	10	40	μΑ
	Supply Current	$I_{OUT} = 0 \ \mu A$					
		V <sub>IN</sub> = 2.4V or 0.5V (Note 4)	0.18	0.3	0.4	0.5	mA

Note 4: This is measured per input with all other inputs held at  $\rm V_{CC}$  or ground.

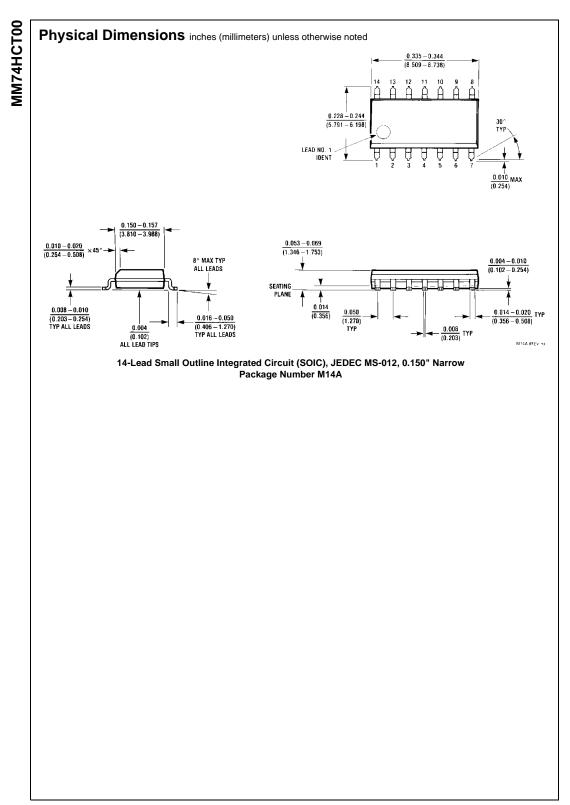
	ctrical Characteristics				
$V_{\rm CC} = 5.0V, 1$	$t_r = t_r = 6 \text{ ns}, C_L = 15 \text{ pF}, T_A = 25^{\circ}\text{C}$ (un	less otherwise noted)			
Symbol	Parameter	Conditions	Тур	Guaranteed Limit	Units
PLH <sup>, t</sup> PHL	Maximum Propagation Delay		14	18	ns

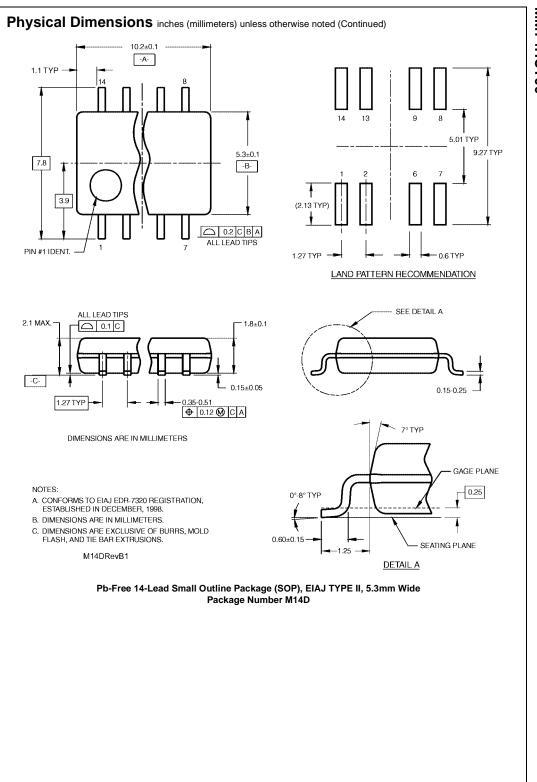
### **AC Electrical Characteristics**

 $V_{CC}$  = 5.0V ±10%, t<sub>r</sub> = t<sub>f</sub> = 6 ns, C<sub>L</sub> = 50 pF (unless otherwise noted)

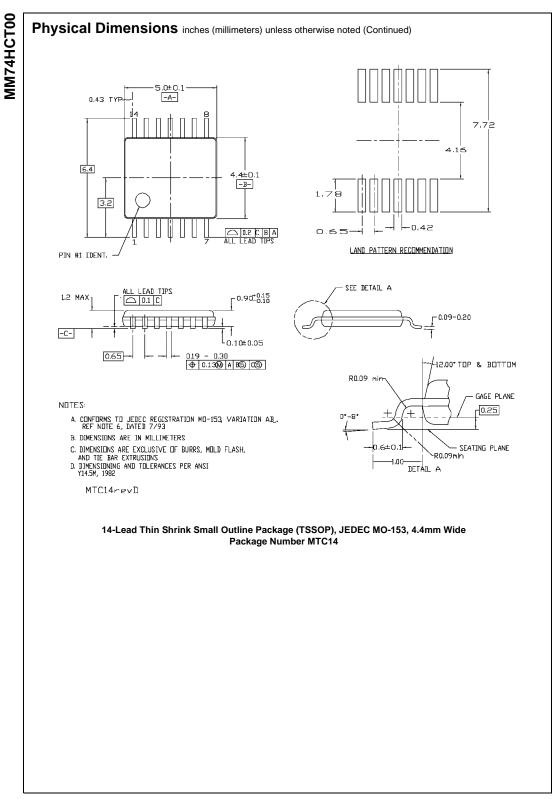
Symbol	Parameter	Conditions	<b>TA</b> =	25°C	$T_A = -40$ to $85^{\circ}C$	$T_A=-55$ to $125^\circ C$	Units
	i arameter		Тур		Guaranteed L	imits	Onits
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay		18	23	29	35	ns
t <sub>THL</sub> , t <sub>TLH</sub>	Maximum Output Rise & Fall Time		8	15	19	22	ns
C <sub>PD</sub>	Power Dissipation Capacitance	(Note 5)	30				pF
CIN	Input Capacitance		5	10	10	10	pF

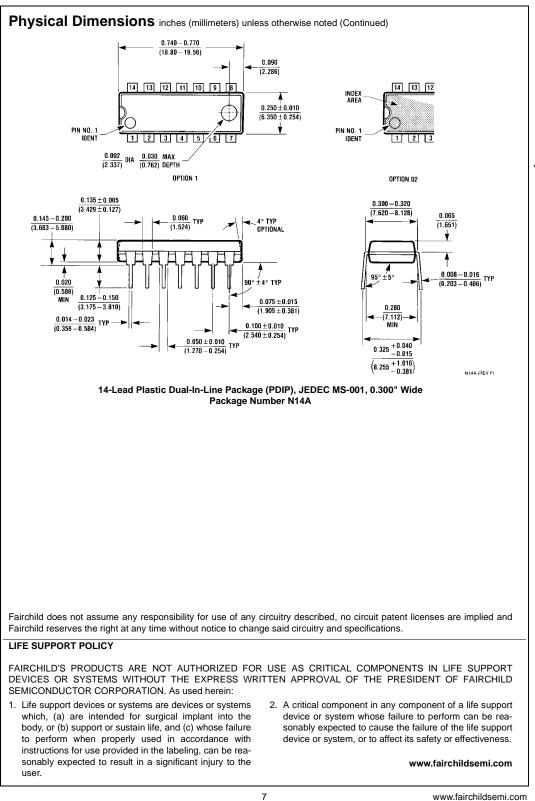
Note 5:  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .





# **MM74HCT00**





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